

N-channel TrenchMOS standard level FET Rev. 02 — 8 July 2010

Product data sheet

Product profile 1.

1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

1.2 Features and benefits

- Higher operating power due to low thermal resistance
- Low conduction losses due to low on-state resistance

1.3 Applications

DC-to-DC convertors

1.4 Quick reference data

Suitable for high frequency applications due to fast switching characteristics

Switched-mode power supplies

Table 1.	Quick reference da	ta					
Symbol	Parameter	Conditions	M	in	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-		-	100	V
I _D	drain current	$T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V}$	-		-	47	А
P _{tot}	total power dissipation	T _{mb} = 25 °C	-		-	150	W
Static cha	aracteristics						
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I _D = 25 A; T _j = 25 °C	-		22	25	mΩ
Dynamic	characteristics						
Q _{GD}	gate-drain charge	V_{GS} = 10 V; I _D = 45 A; V _{DS} = 80 V; T _j = 25 °C	-		25	-	nC

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2. Pinning information

Table 2.	Pinning information				
Pin	Symbol	Description	Simplified outline	Graphic symbol	
1	G	gate	_	<u>_</u>	
2	D	drain ^[1]	mb		
3	S	source			
mb	D	mounting base; connected to drain		mbb076 S	
			SOT404 (D2PAK)		

[1] It is not possible to make connection to pin 2.

3. Ordering information

Table 3.Ordering information

Type number	Package		
	Name	Description	Version
PHB45NQ10T	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

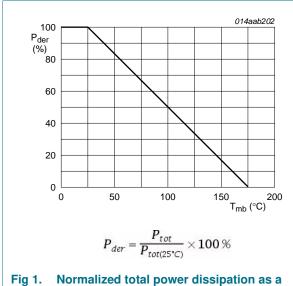
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4. Limiting values

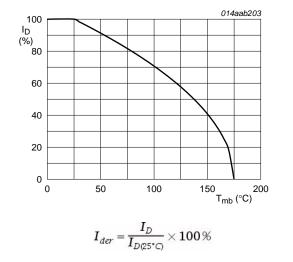
Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	100	V
V _{DGR}	drain-gate voltage	T _j ≤ 175 °C; T _j ≥ 25 °C; R _{GS} = 20 kΩ	-	100	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	$V_{GS} = 10 \text{ V}; \text{ T}_{mb} = 100 \text{ °C}$	-	33	А
		$V_{GS} = 10 \text{ V}; \text{ T}_{mb} = 25 \text{ °C}$	-	47	А
I _{DM}	peak drain current	pulsed; T _{mb} = 25 °C	-	188	А
P _{tot}	total power dissipation	T _{mb} = 25 °C	-	150	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-drai	n diode				
I _S	source current	T _{mb} = 25 °C	-	47	А
I _{SM}	peak source current	pulsed; T _{mb} = 25 °C	-	188	А
Avalanche r	uggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$ \begin{array}{l} V_{GS} = 10 \text{ V}; T_{j(init)} = 25 \ ^{\circ}\text{C}; \text{I}_{\text{D}} = 40 \text{ A}; \\ V_{sup} \leq 25 \text{ V}; \text{ unclamped}; \text{t}_{p} = 100 \ \mu\text{s}; \\ R_{GS} = 50 \ \Omega \end{array} $	-	260	mJ
I _{AS}	non-repetitive avalanche current	$V_{sup} \le 25 \text{ V}; V_{GS} = 10 \text{ V}; T_{j(init)} = 25 \text{ °C};$ $R_{GS} = 50 \Omega;$ unclamped	-	47	А



function of mounting base temperature





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10

t_{AV} (ms)

25

1

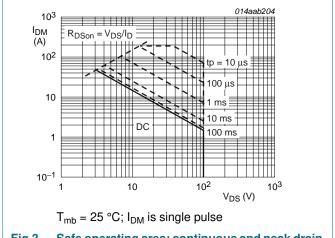
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T_j prior to avalanche = 150 °C

10⁻¹

Single-shot avalanche rating; avalanche

current as a function of avalanche period





5. Thermal characteristics

Table 5.Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base		-	-	1	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	mounted on printed-circuit board ; minimum footprint	-	50	-	K/W

10²

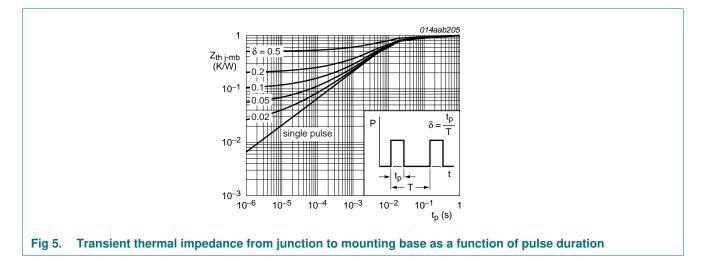
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1 10⁻³

Fig 4.

10⁻²

I_{AS} (A)



N-channel TrenchMOS standard level FET

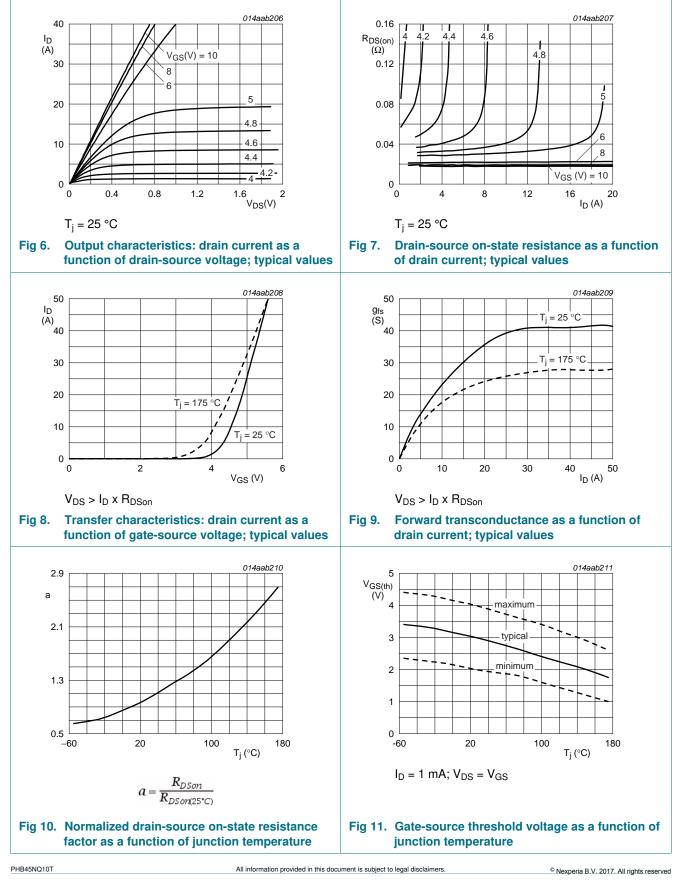
6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static cha	aracteristics					
V _{(BR)DSS} dr	drain-source	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	89	-	-	V
	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	100	-	-	V
V _{GS(th)}	gate-source threshold	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$	-	-	6	V
	voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C}$	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	2	3	4	V
I _{DSS}	drain leakage current	$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μA
		$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μA
I _{GSS}	gate leakage current	$V_{GS} = 10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	100	nA
		$V_{GS} = -10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	100	nA
R _{DSon}	drain-source on-state	V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C	-	-	68	mΩ
	resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C	-	22	25	mΩ
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 45 \text{ A}; V_{DS} = 80 \text{ V}; V_{GS} = 10 \text{ V};$	-	61	-	nC
Q _{GS}	gate-source charge	$T_j = 25 \text{ °C}$	-	13	-	nC
Q _{GD}	gate-drain charge		-	25	-	nC
C _{iss}	input capacitance	$V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	2600	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	340	-	pF
C _{rss}	reverse transfer capacitance		-	195	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 50 \text{ V}; \text{ R}_{L} = 1.8 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	18	-	ns
t _r	rise time	$R_{G(ext)} = 5.6 \ \Omega; T_j = 25 \ ^{\circ}C$	-	72	-	ns
t _{d(off)}	turn-off delay time		-	69	-	ns
t _f	fall time		-	58	-	ns
L _D	internal drain inductance	from tab to centre of die ; $T_j = 25 \text{ °C}$	-	3.5	-	nH
L _S	internal source inductance	from source lead to source bond pad ; $T_j = 25 ^\circ\text{C}$	-	7.5	-	nH
Source-d	rain diode					
V _{SD}	source-drain voltage	$I_{S} = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_{j} = 25 \text{ °C}$	-	0.87	1.2	V
t _{rr}	reverse recovery time	$I_{S} = 20 \text{ A}; dI_{S}/dt = -100 \text{ A}/\mu s; V_{GS} = 0 \text{ V};$	-	82	-	ns
Q _r	recovered charge	V _{DS} = 25 V; T _j = 25 °C	-	0.26	-	μC

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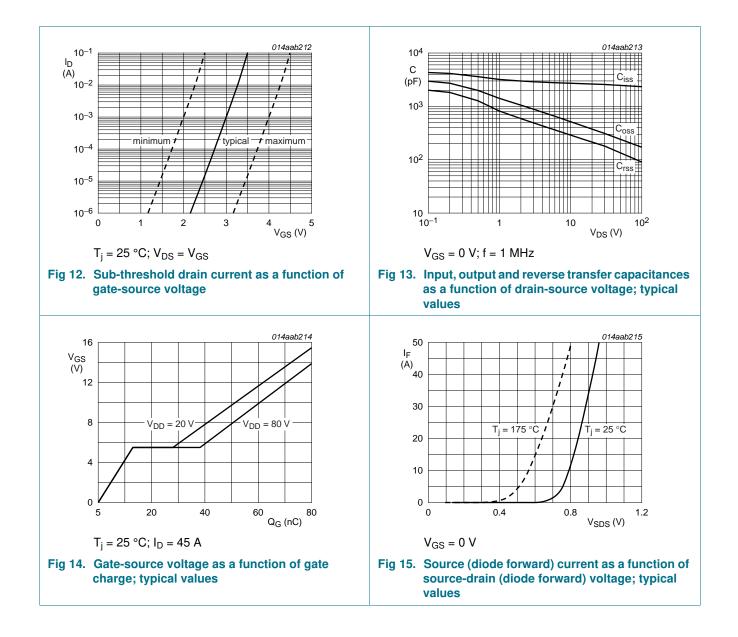
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7. Package outline

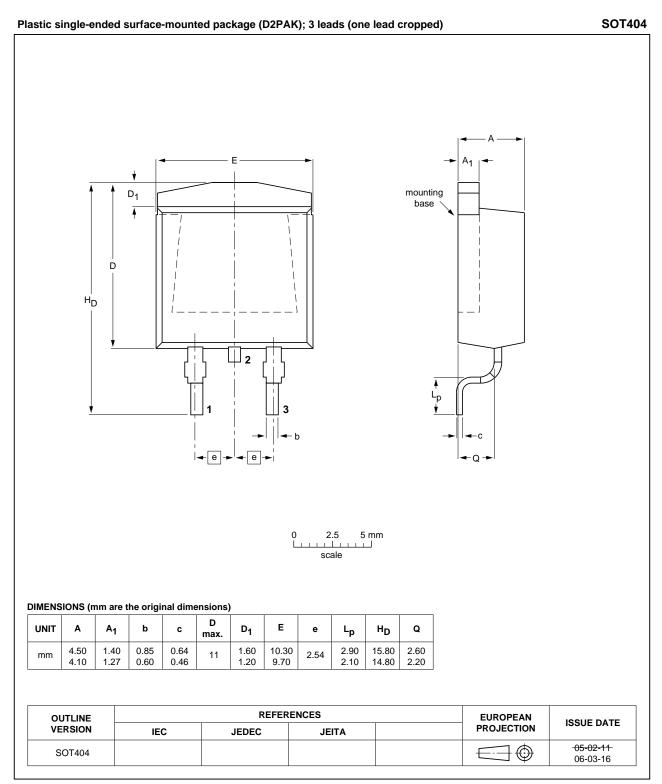


Fig 16. Package outline SOT404 (D2PAK)

PHB45NQ10T Product data sheet

N-channel TrenchMOS standard level FET

8. Revision history

Table 7.	Revision history						
Document ID		Release date	Data sheet status	Change notice	Supersedes		
PHB45NQ	10T v.2	20100708	Product data sheet	-	PHB_PHP_PHW45NQ10T v.1		
Modifications:		 The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. 					
		 Legal texts hat 	ve been adapted to the	new company na	ame where appropriate.		
		Type number	PHB45NQ10T separate	ed from data shee	t PHB_PHP_PHW45NQ10T v.1.		
PHB_PHP	_PHW45NQ10T v.1	19990801	Product specification	-	-		

N-channel TrenchMOS standard level FET

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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N-channel TrenchMOS standard level FET

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N-channel TrenchMOS standard level FET

11. Contents

1	Product profile1
1.1	General description1
1.2	Features and benefits1
1.3	Applications1
1.4	Quick reference data1
2	Pinning information2
3	Ordering information2
4	Limiting values
5	Thermal characteristics4
6	Characteristics5
7	Package outline8
8	Revision history9
9	Legal information10
9.1	Data sheet status10
9.2	Definitions10
9.3	Disclaimers
9.4	Trademarks11
10	Contact information11